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#6/Amend A
DKing
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: FURUHATA et al.)
Serial No.: 09/604,702)
Filed: June 23, 2000)
For: SEMICONDUCTOR DEVICES HAVING A)
NON-VOLATILE MEMORY TRANSISTOR)

Group Art Unit: 2812

Examiner: Booth, R.

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AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sirs:

In response to the Office Action dated November 8, 2001, the time for response being extended to May 8, 2002 by the enclosed petition for extension of time, please enter and consider the following:

IN THE CLAIMS:

Please insert new claims 24-29 as follows:

Sub B
A1
~~--24. (new) A semiconductor device as in claim 21, wherein the third voltage-type transistor has a gate insulation layer formed from at least three insulation layers, wherein the at least three insulation layers of the third voltage type transistor are identical in composition to the at least three insulation layers of the intermediate insulation layer of the non-volatile memory transistor.~~

25. (new) A semiconductor device as in claim 21, wherein the first voltage-type transistor has a gate insulation layer having a thickness that is less than that of the second voltage-type transistor, and the second voltage-type transistor has a gate insulation layer having a thickness that is less than that of the third voltage type transistor.

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